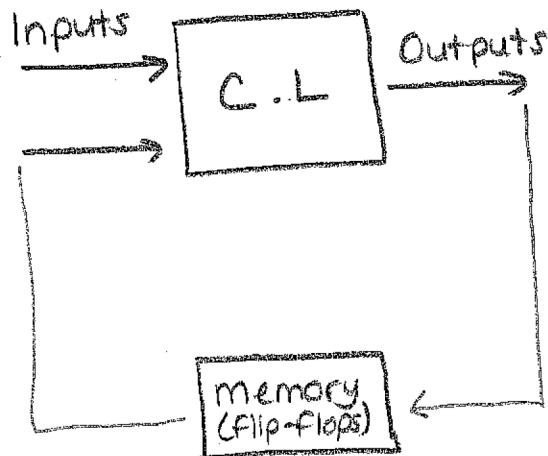


## finite state machines: (Sequential Digital Circuits)



\* In combinational logic circuits (C.L.), we have inputs, output, gates.

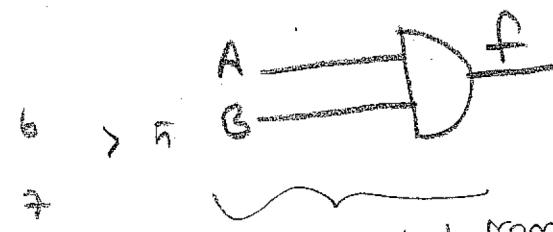
Ex: (C.L.)

Design a C.L. circuit that outputs a "1" when the value of the inputs  $ABC > 5$  in decimal.

most significant bit (MSB)      least sign. bit (LSB)

A	B	C	f
0	0	0	0
0	0	1	0
0	1	0	0
0	1	1	0
1	0	0	0
1	0	1	0
1	1	0	1
1	1	1	1

BC		00	01	11	10
A'	0	0	0	0	0
A	1	0	0	1	1

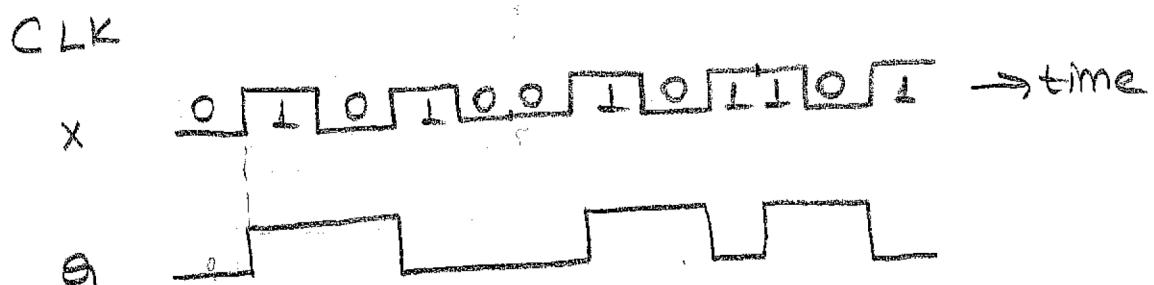


\* independent from C.

## STEPS (for prev. ex.)

- Draw Table
- K-Map
- Simplify Function
- Draw the circuit

Ex: Assert output whenever input bit stream has  
odd # of 1's.



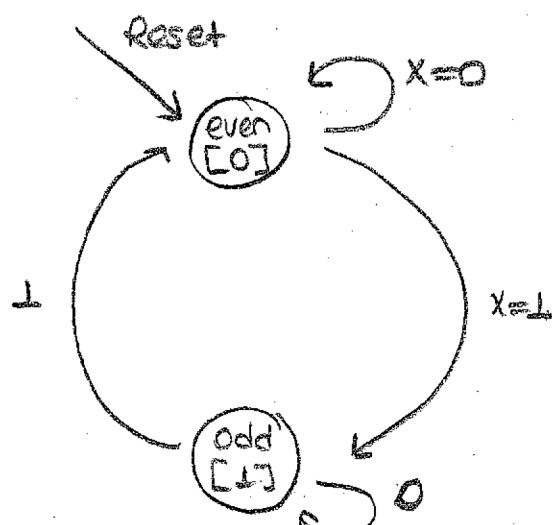
## STEPS

- 1) Understand the problem
- 2) Draw the state diagram
- 3) Construct the transition table  
↳ state
- 4) Simplify the table
- 5) Draw the circuit

## Answer:

- 2) State Diagram

State:  
output value

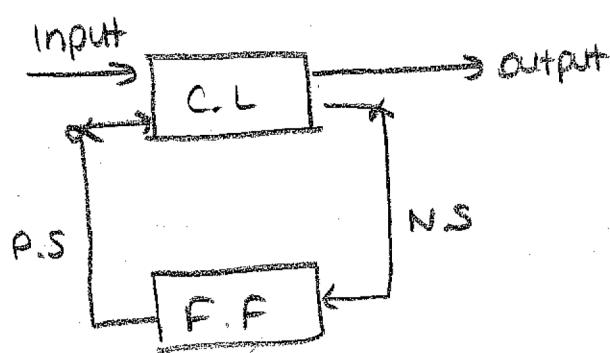


3) State Transition Table: output determined according to the P.S

Present State (P.S)	Input (X)	Next State (N.S.)	Output
0	0	0	0
0	1	1	0
1	0	1	1
1	1	0	1

Determined at the P.S.

4)

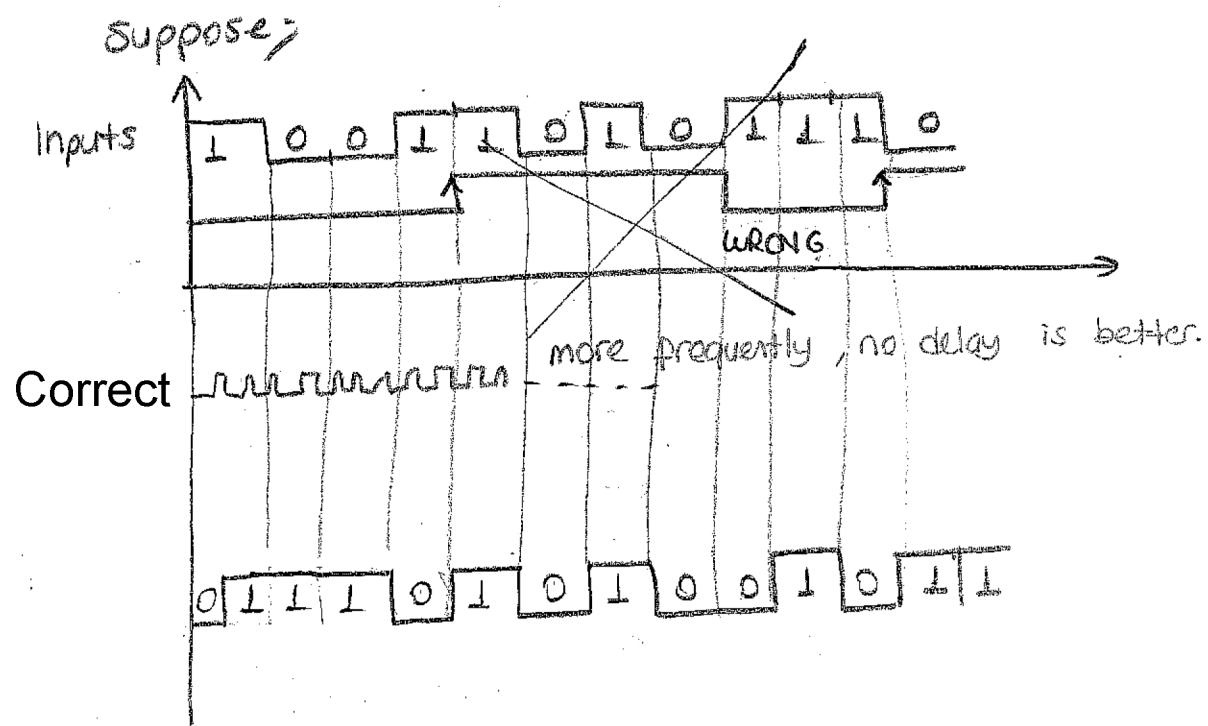
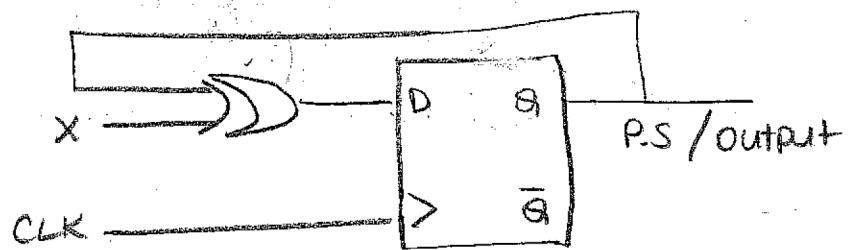


Assume D-FF implementation

P.S $\Rightarrow$ D <sub>1</sub>	X	N.S $\Rightarrow$ Q <sub>1</sub>
0	0	0
0	1	1
1	0	1
1	1	0

$$Q_1 = D_1 \oplus X$$

↓  
XOR



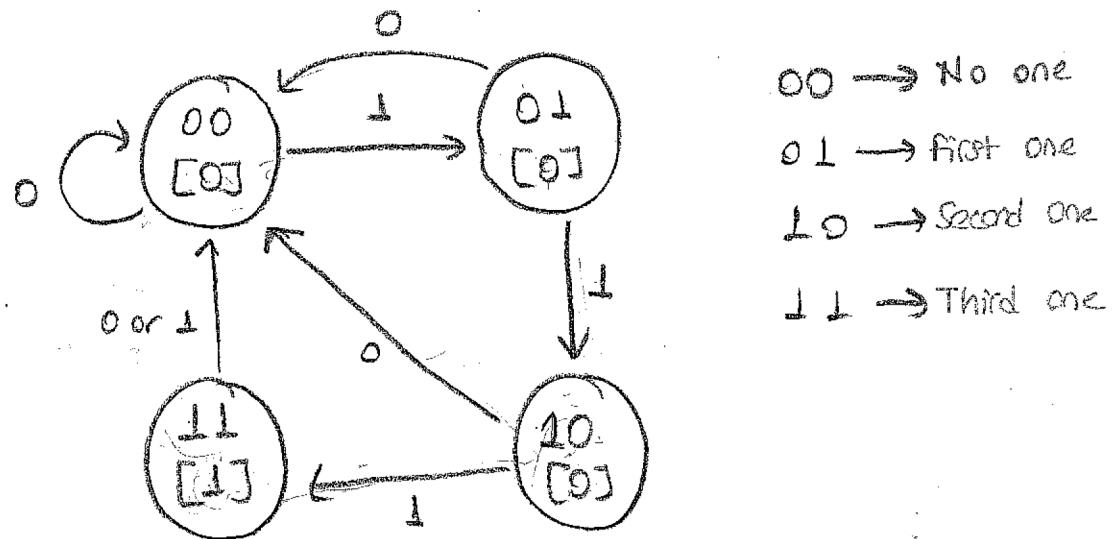
Ex: Design of vending machine.

- Deliver a package of gum after 15 ₦
- Single coin slot
- 1₦ ₦ and 0.5 ₦
- No change (geri verme yok)

## Lab. Question Answer:

Her 3'de 1 yopacak sonra 0.

Diagram:



Step 3: State transition Table

P.S $\theta_1 \theta_0$	Input X	N.S		Output Z
		$\theta_1$	$\theta_0$	
0 0	0	0	0	0
00	1	0	1	0
0 1	0	0	0	0
0 1	1	1	0	0
1 0	0	0	0	0
1 0	1	1	1	0
1 1	0	0	0	1
1 1	1	0	0	1

(D<sub>1</sub>)

X	$\bar{Q}_1 Q_0$	00	01	11	10
0	0	0	0	0	0
1	0	1	0	1	1

$$D_1 = \frac{1}{2} \rightarrow \text{No simplification}$$

$$= X \cdot \bar{Q}_1' \cdot Q_0 + X \cdot Q_1 \cdot \bar{Q}_0'$$

(D<sub>0</sub>)

X	$\bar{Q}_1 Q_0$	00	01	11	10
0	0	0	0	0	0
1	1	0	0	1	1

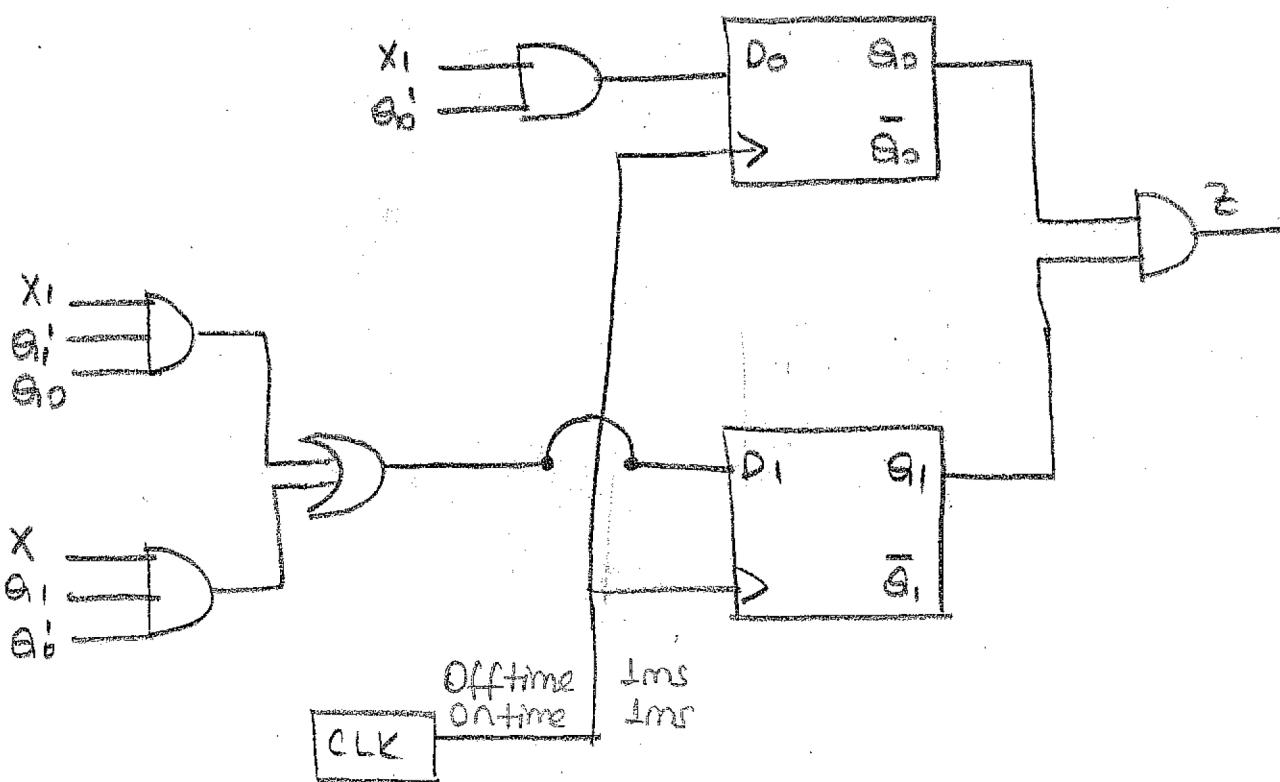
$$D_0 = \frac{1}{2} \rightarrow X \cdot \bar{Q}_0'$$

(Z)

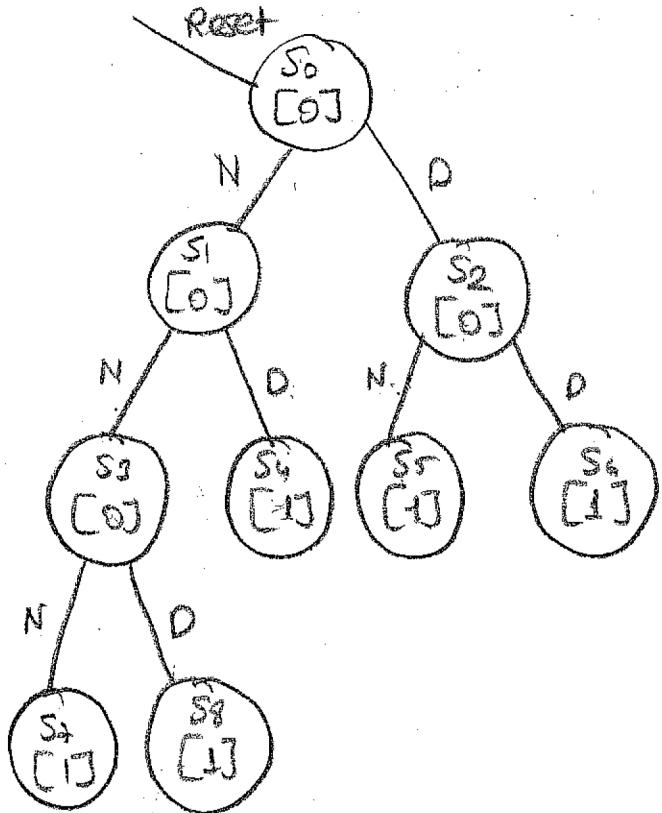
X	$\bar{Q}_1 Q_0$	00	01	11	10
0	0	0	0	1	0
1	0	0	1	0	0

$$Z = \rightarrow \bar{Q}_1 \cdot \bar{Q}_0$$

Circuit Implementation:

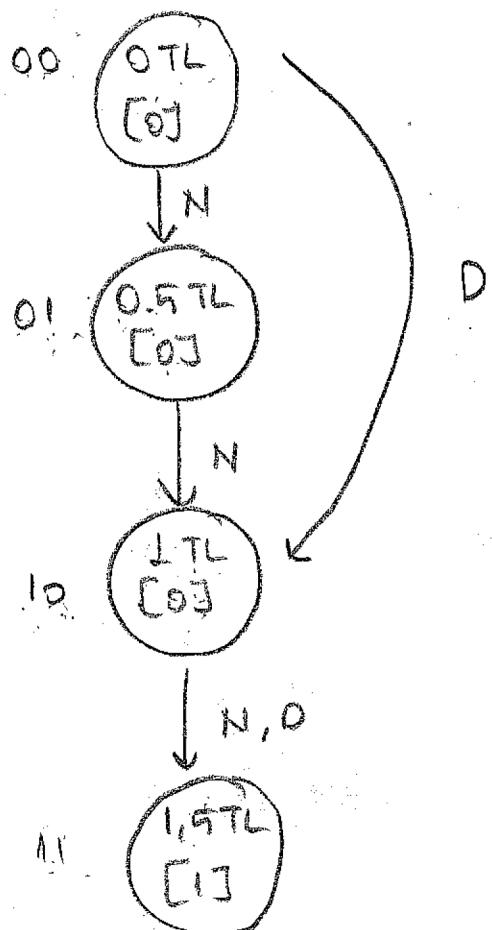


## Vending machine



$1 TL = 0$

$0.5 TL = N$



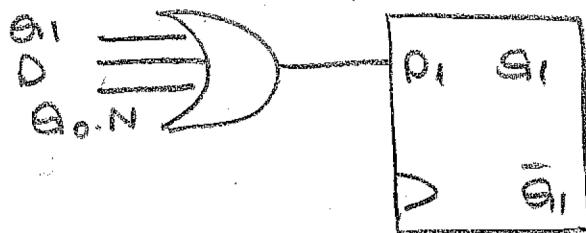
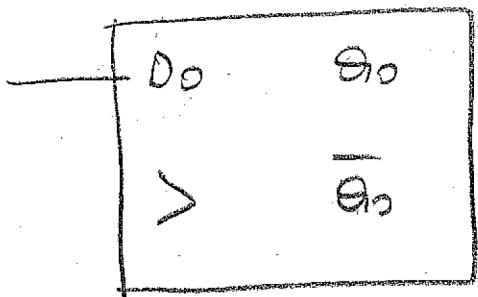
P.S $Q_1, Q_0$	Inputs D.N	N.S $D_1 D_0$	Outputs
0.0	00	0 0	0
	01	0 1	0
	10	1 0	0
	11	X X	
0.1	00	0 1	0
	01	1 0	0
	10	1 1	0
	11	X X	X

$Q_1, Q_0$	D.N	D <sub>1</sub> D <sub>0</sub>	Outputs
1 0	00	1 0	0
	01	1 1	0
	10	1 1	0
	11	X X	X
D <sub>1</sub>	00	1 1	1
	01	1 1	1
	10	1 1	1
	11	X X	X

$$D_1 = Q_1 + D + Q_0 N$$

$$D_0 = N \bar{Q}_0 + Q_0 \bar{N} + Q_1 N + Q_1 D$$

$$\text{Output} = Q_1, Q_0$$



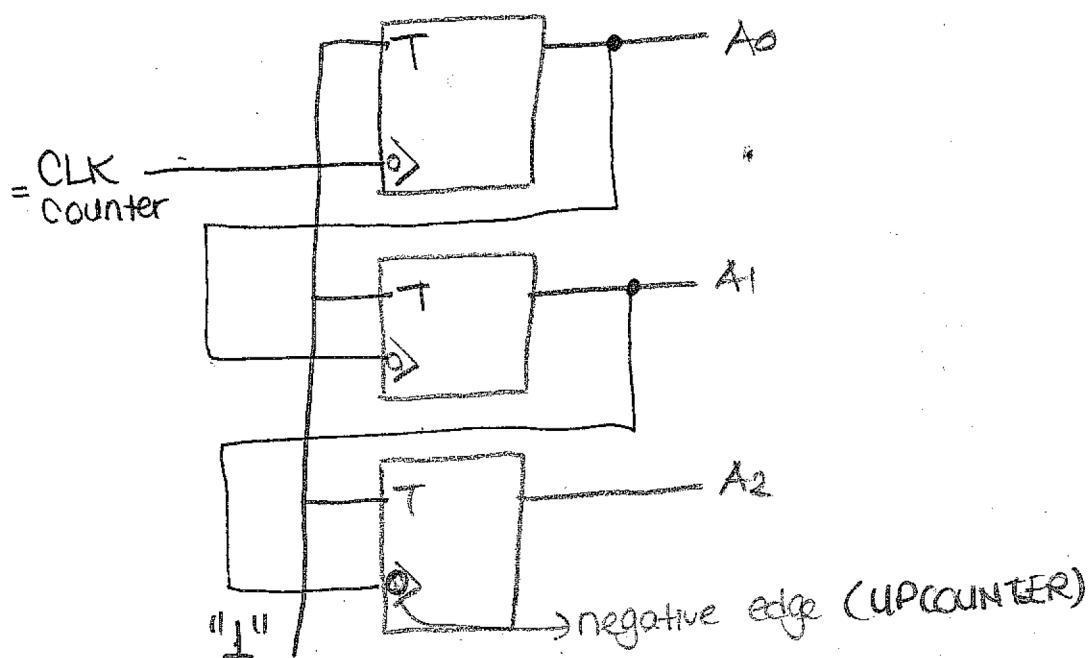
## CH: 6 REGISTERS & COUNTERS

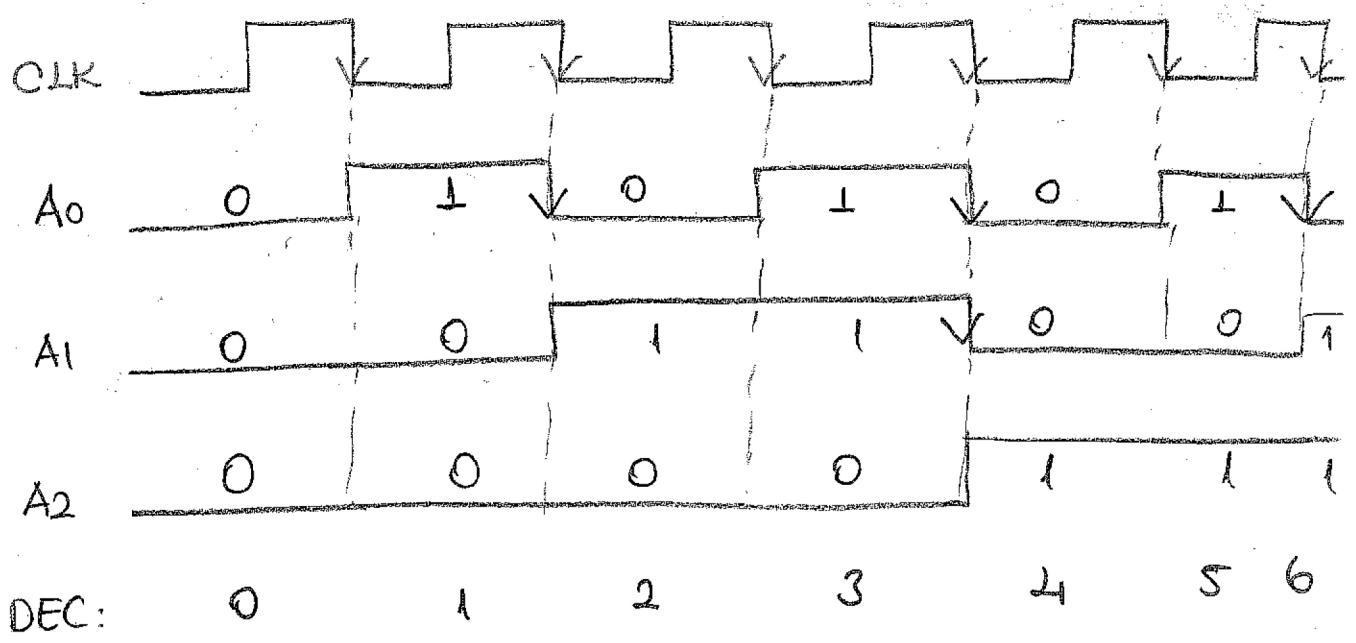
Counters: circuit that follows the binary number sequence.

↘ Ripple Counters      ↘ Synchronous Counters

Ripple Counter:

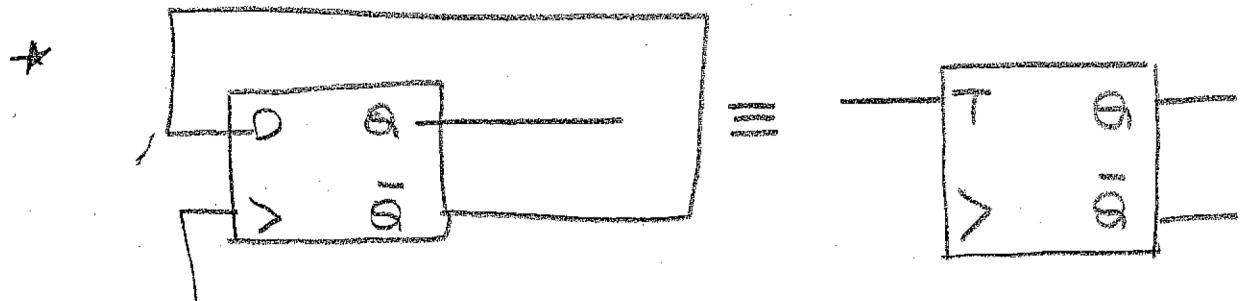
Using TFF





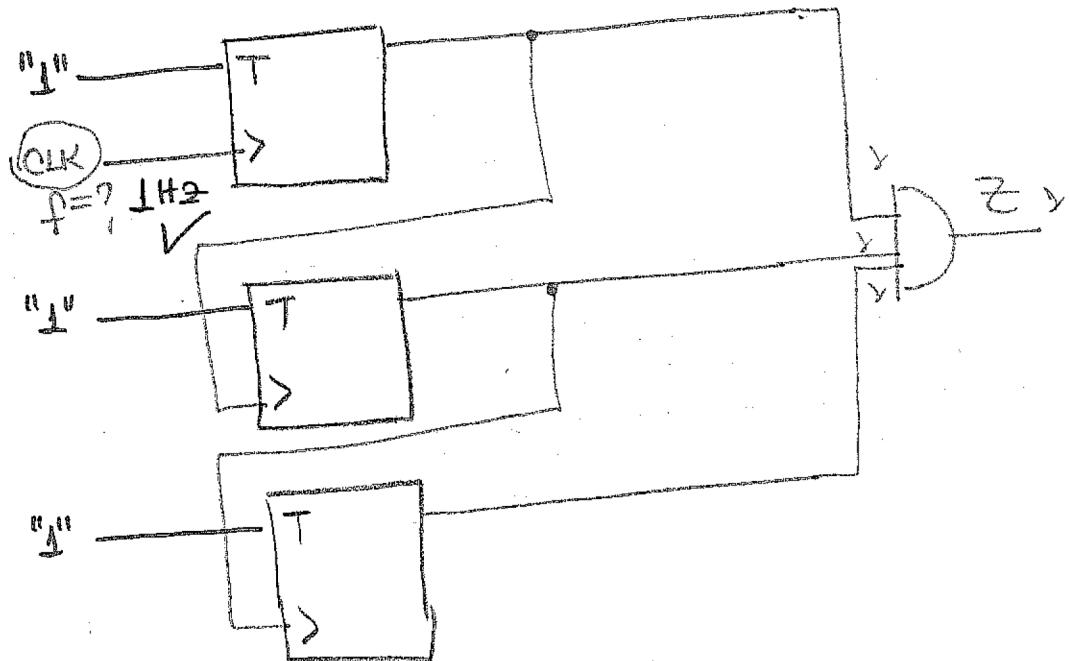
NOT: If we use (+) edge TFF's, then we obtain down counters.

Also note that DFF if you connect



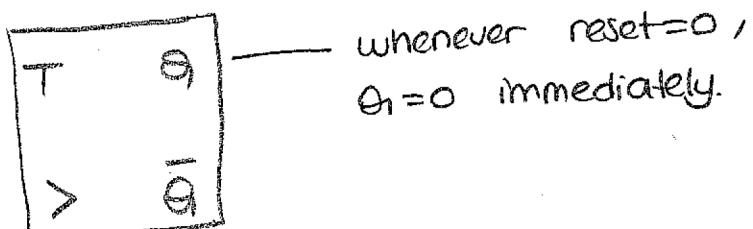
Ex: Design a counter circuit that waits for 8 seconds and outputs a "1".

Ans: Use the TFF counter as before.



Question: What if we want to make it count to a certain number?

Then, one possible solution is to use FF's with reset such as,



whenever reset=0,  
 $Q_1=0$  immediately.

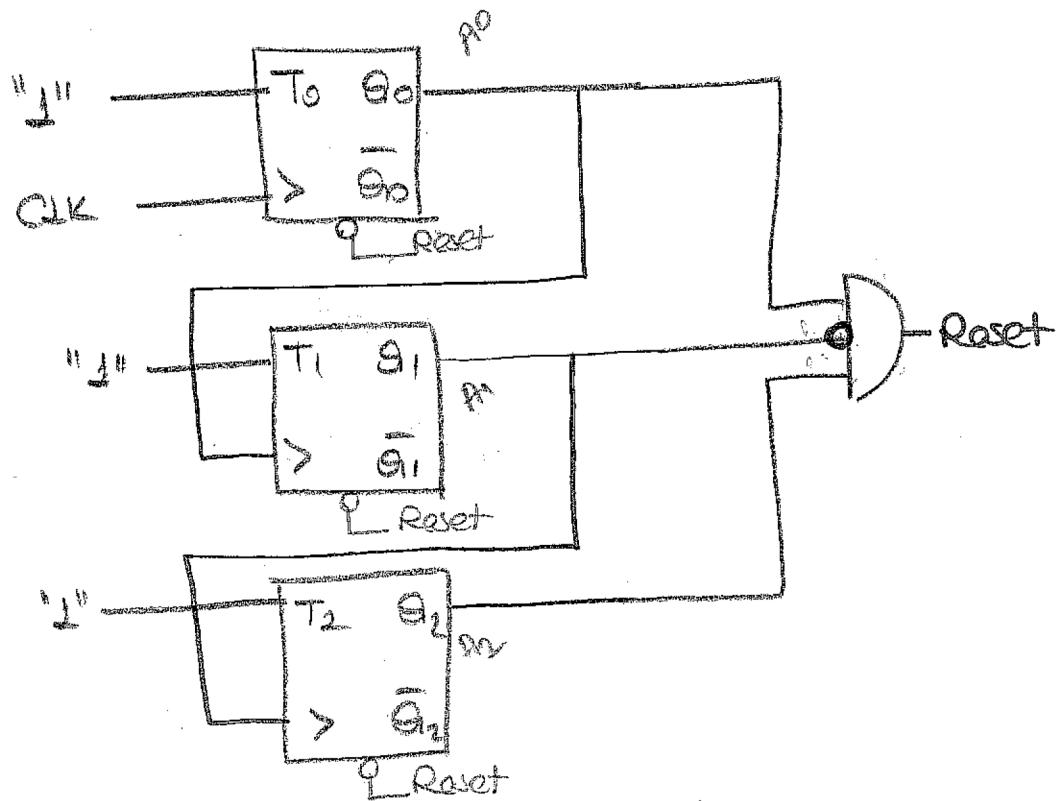
Reset (if it's zero, outputs are zero)

Ex: Design a ripple counter that counts to decimal 5.

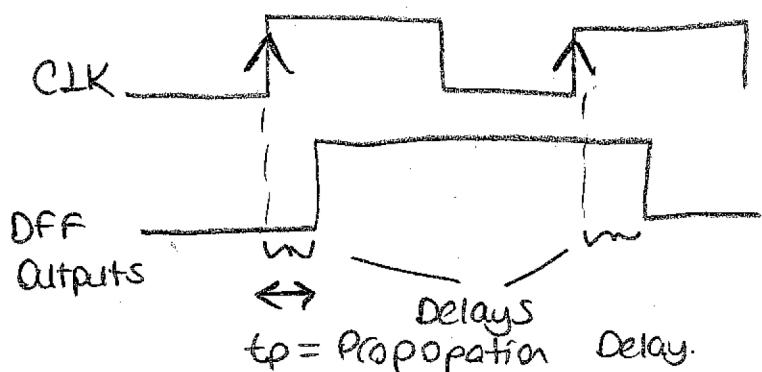
Ans:

$$5 = 101$$

000, 001, 010, 011, 100, 101, 000



⚠ Ripple counters are problematic in the way that  
they generate delays.



The remedy is to use:

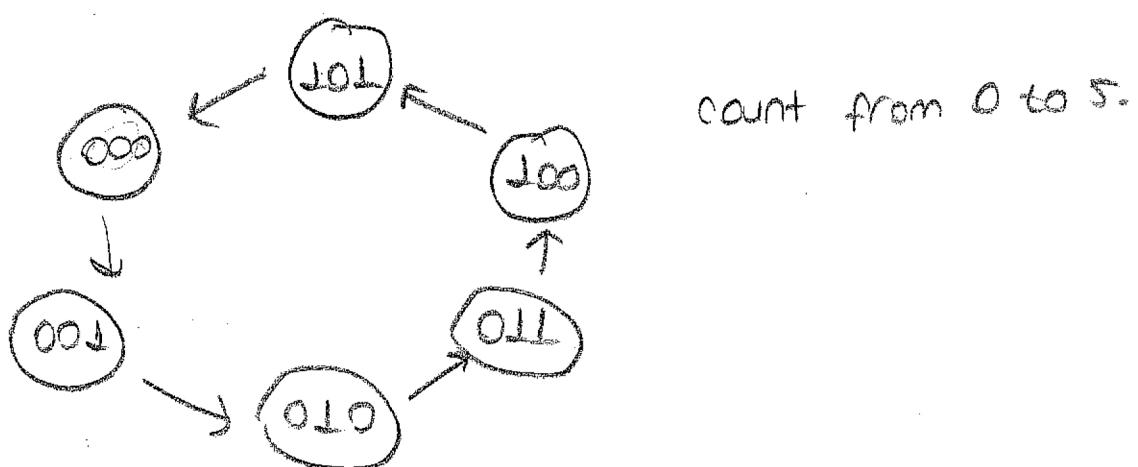
### Synchronous Counters:

We can use the first design techniques for synchronous counter design.

Ex: Design a sync counter that counts,  
000, 001, 010, 011, 100, 101, 000...

Ans:

State Diagram: (No input)



$Q_2 Q_1 Q_0$ P.S	D0 D1 D0 N.S	Output
000	001	0
001	010	0
010	011	0
011	100	0
100	101	1
101	000	0
110	111	0
111	000	0

# MEMORY & REGISTERS

Register: 1 bit storage device (ff)

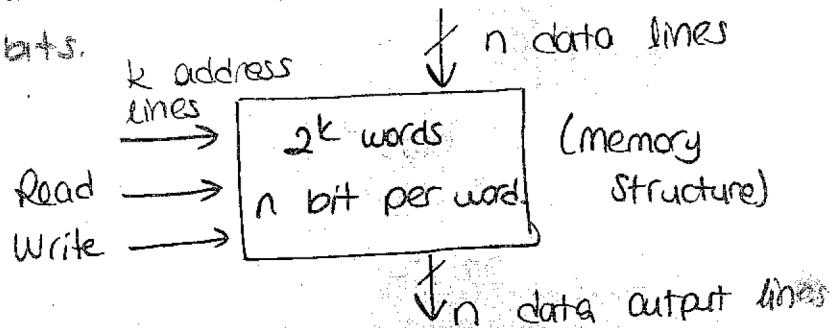
memory → Random Access memory (RAM):  
→ Read-Only memory (Rom):

RAM:

Definitions:

words = binary information in groups.

Byte: Groups of 8 bits.



Memory Address	Memory Content
0	00000000
1	00000001
2	00000010
3	00000011
...	...
1023	11111111

Address  $\rightarrow 0 - 2^k - 1$  where  $k$  is # of address lines

Ex: How many bytes does a memory with 1K words of 16 bits each can support?

Ans:

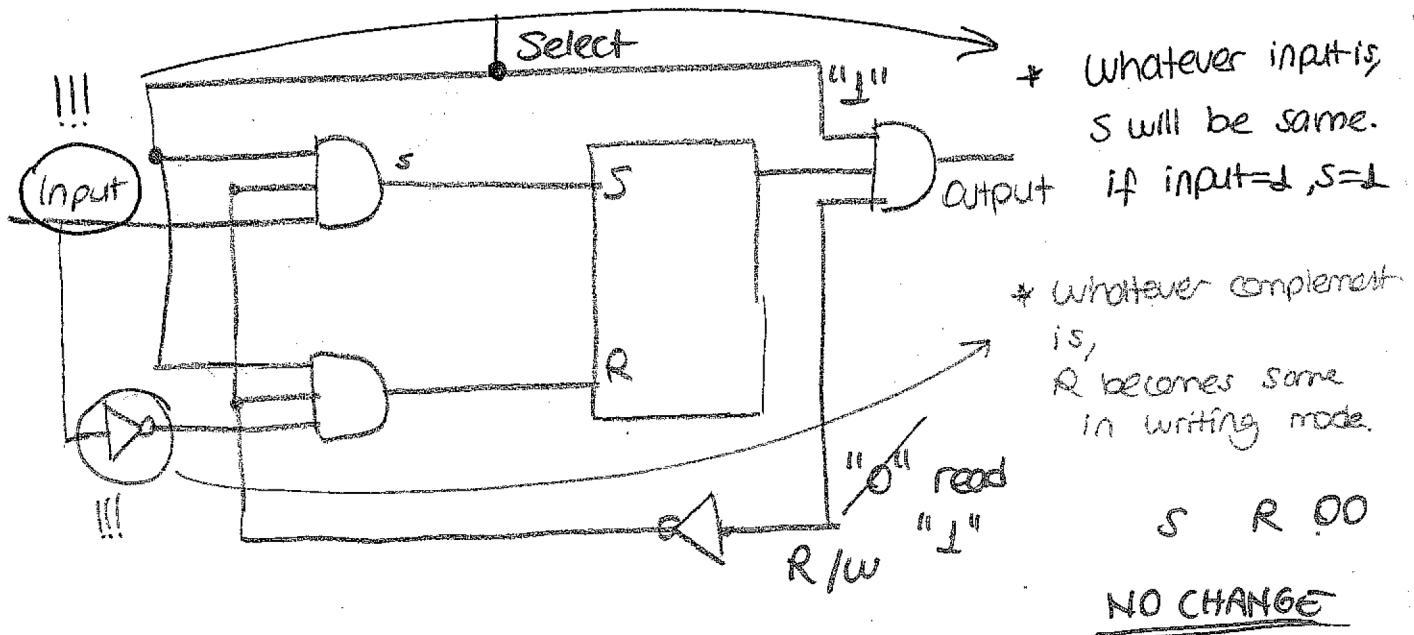
$$1K = 1024 = 2^{10}$$

Since each word contains 16 bit = 2 bytes

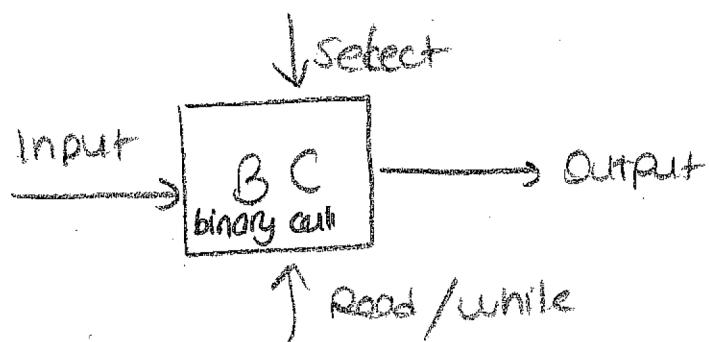
$$\Rightarrow 1K \times 2 = 2K = 2048 \text{ bytes}$$

### Internal Construction of RAM:

RAM with  $m$  words and  $n$  bits per word consists of  $m \times n$  binary storage cells. (bsc)



We can also show it as,



\* BC stores a bit

select=0 , output=0

when select=1 , R/w mode is enabled

↳ If R/w=0:

Write is performed

↳ If R/w=1:

Read is performed

In reading mode, Latched,  
does not change

(The data inside BC, is latched).

Ex: Design a 4x4 RAM

each word contains 4 bits.



→ word 1



1 2



3

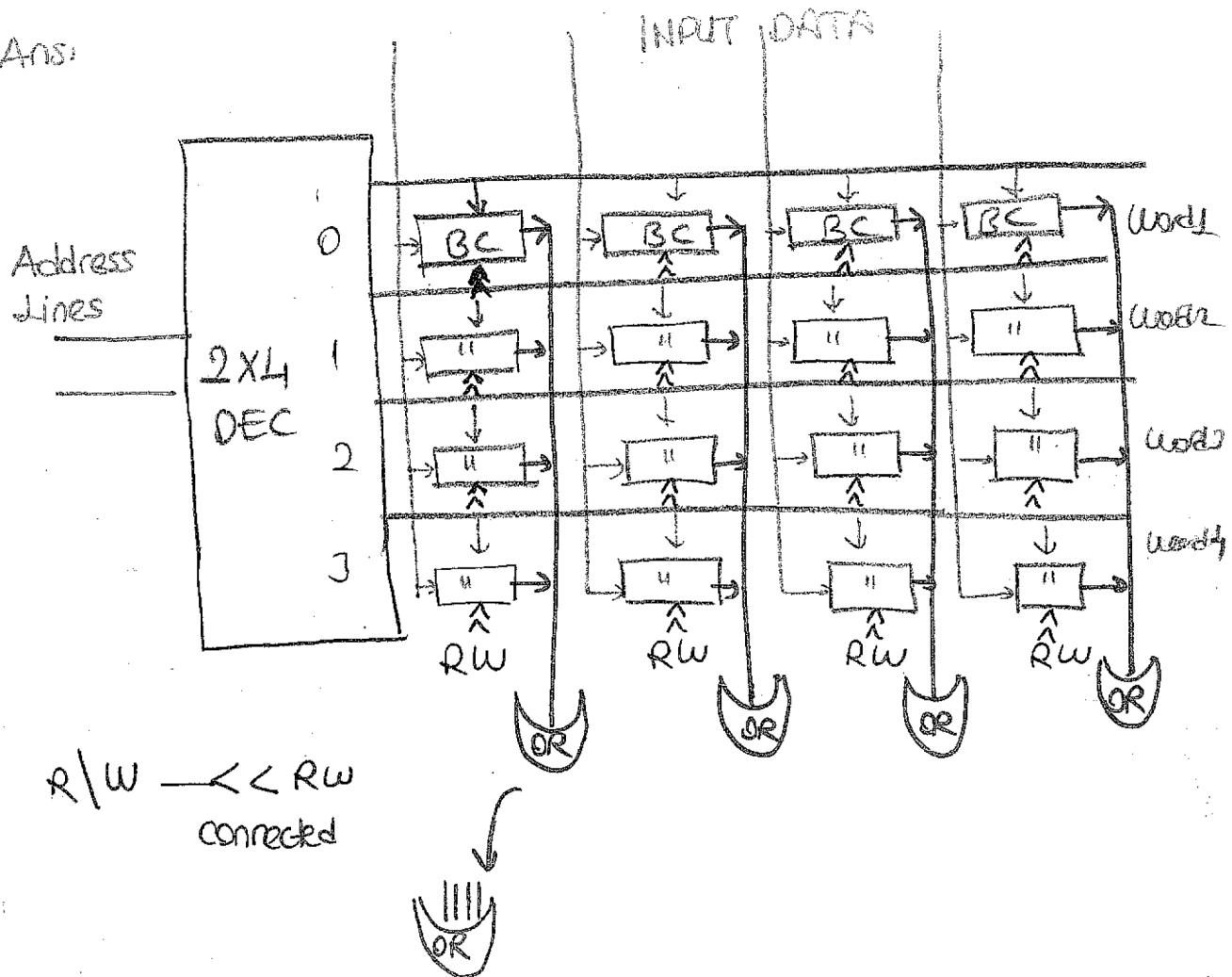


4

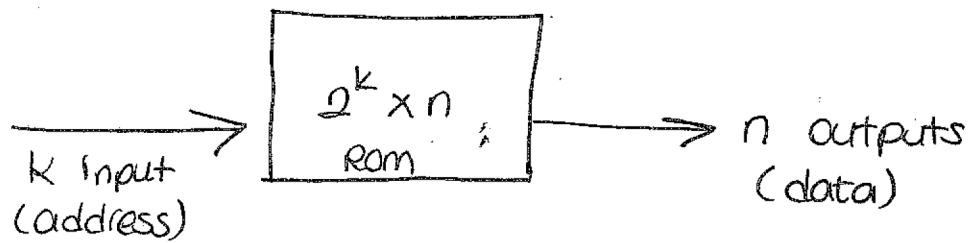
ans



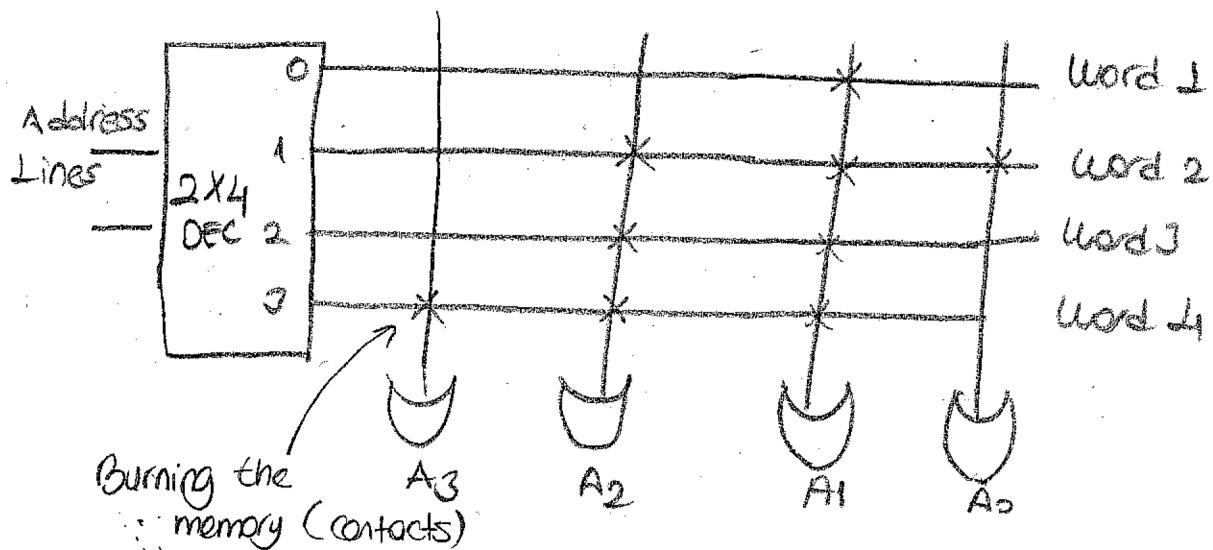
Ans:



## Read Only Memory (Rom)



Ex: Design a 4x4 Rom and store 0010, 0111, 0110, 1110.



- \* In Rom , once you write, you can't change it
- ROM is not erasible (silinebilir). The data is permanent  
The read speed is fast
- RAM is erasible , R/W is possible . The read / write speed is slower than Rom.
- If we modify a Rom to be erasible; This is called EPRom  
To erase EPRom, one needs to put it on UV light.

— There is also a 2<sup>nd</sup> type of erasable Rom.

~~E~~<sup>EEP</sup>ROM or E<sup>2</sup>PROM (transistors, switches...)

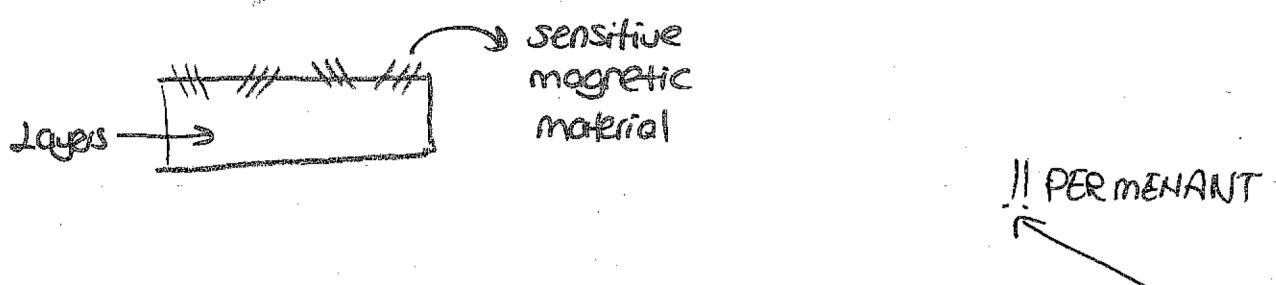
The difference from EEPROM is that instead of using UV light to erase the memory, we use electrical signals?

RAM: All these RAM and Rom are semiconductor memories. *(Yoni Notkin)*  
by electronic devices.

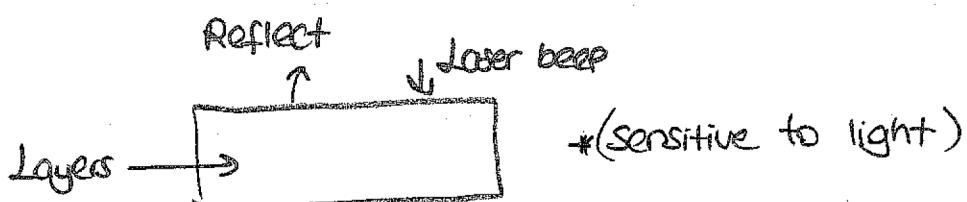
Non-volatile memory: When the power is off, the data remains inside the memory.

Other non-volatile memories:

1) Hard-disk: magnetic field based operation.

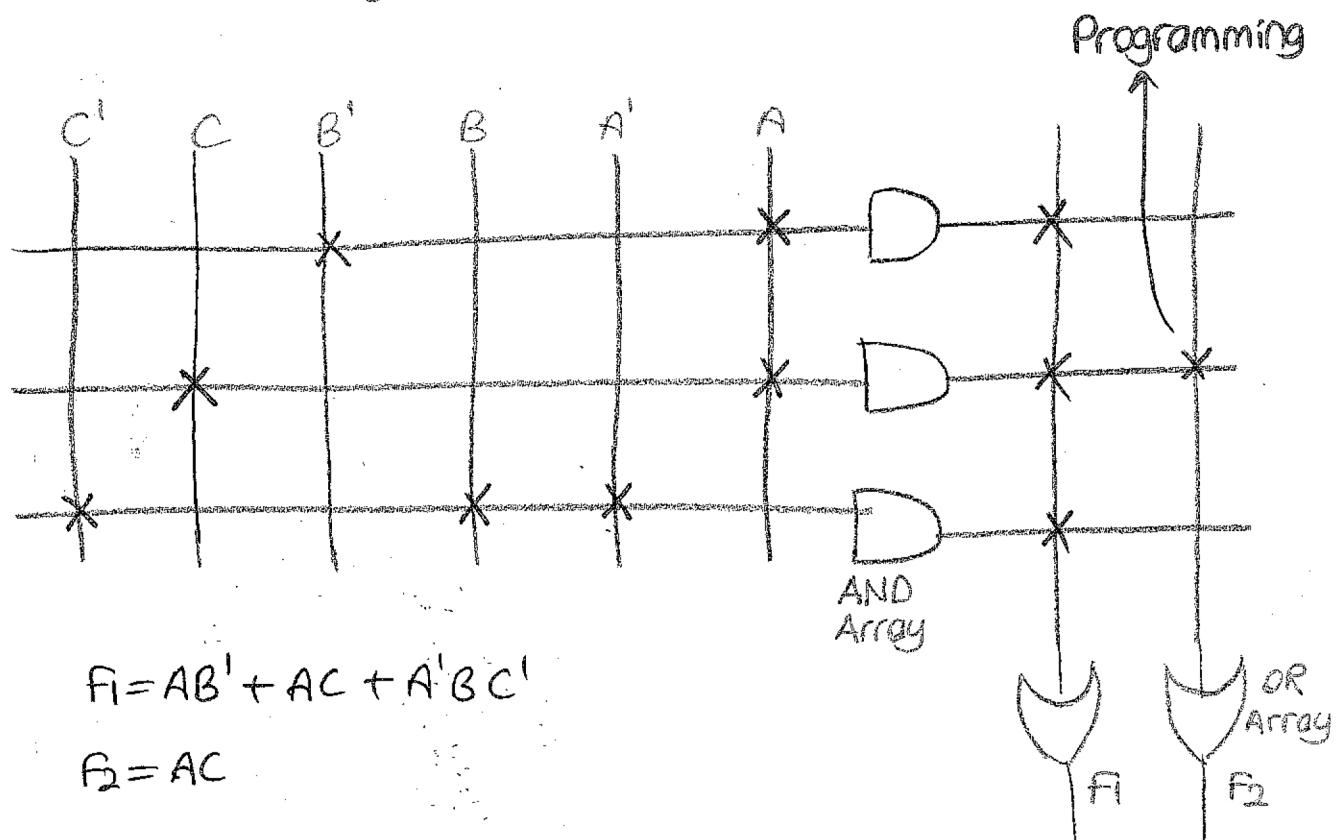


2) CD-Rom, DVD-Rom: Optical waves are used

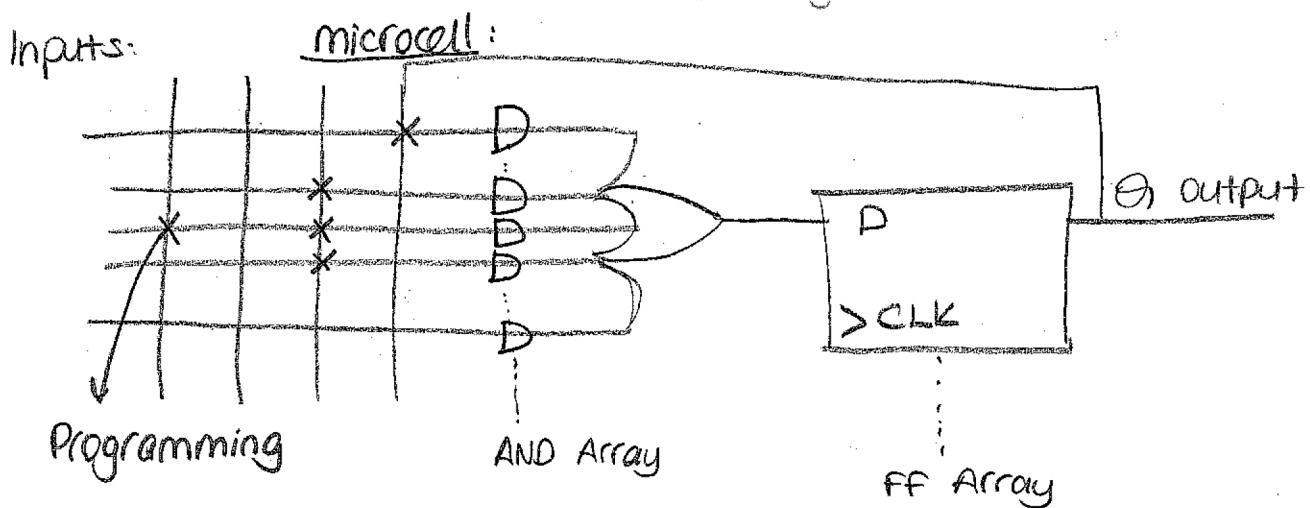


## PLD's: Programmable Logic Devices:

### PLA: Programmable Logic Array:

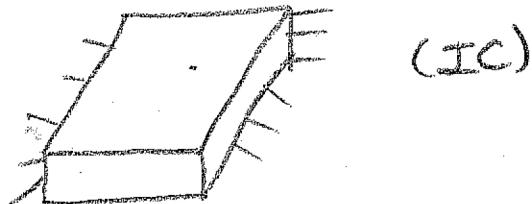
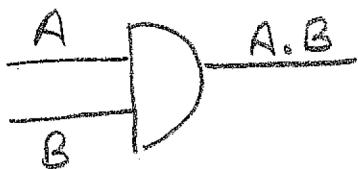


### SPLD: Sequential Prog. Logic Devices:



FPGA: field Programmable Gate Array

↓  
Electric field



Digital Integrated Circuits:

IC Digital Logic Families:

DTL - Diode - Transistor Logic

TTL - Transistor - Transistor Logic

MOS - Metal - Oxide Semiconductor

CMOS - Complementary Metal - Oxide Semiconductor

|

RTL, ECL ...

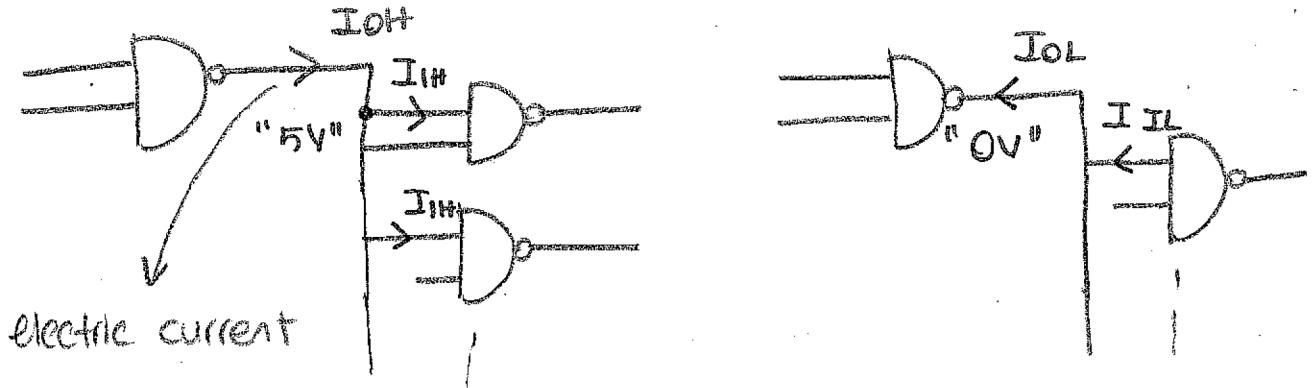
Special Characteristics:

1) Fan-out:

max. number of gates that can be connected to a single gate.

$$\text{Fanout} = \frac{|I_{O+}|}{|I_{I+}|} = \frac{|I_{O-}|}{|I_{I-}|}$$

↓ output high      ↓ output low  
 ↑ input high      ↑ input low



Ex: Given,  $I_{OH} = 400\mu A$ ,  $I_{LH} = 40\mu A$ ,  $I_{OL} = 16mA$ ,  
 $I_{LL} = 1.6mA$ . Find the fan-out.

$$F.O = \frac{400\mu A}{40\mu A} = 10$$

$$\frac{16mA}{1.6mA} = 10$$

Power Dissipation:

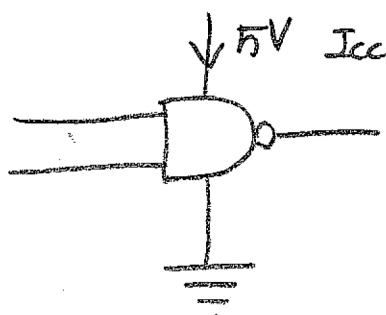
$$I_{CC}(\text{avg}) = \frac{I_{CCH} + I_{CCL}}{2}$$

where  $I_{CL}$  = current

$$\text{Power Consumption} = P_D(\text{avg}) = I_{CC}(\text{avg}) \times V_{CC}$$

Ex: Find the ave power dissipation of a standard TTL.

NAND gate that uses a supply voltage of 5V.



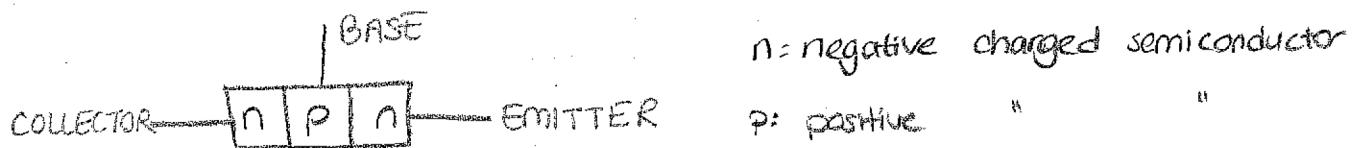
$$I_{CC} = 3mA$$

$$I_{CCH} = 1mA$$

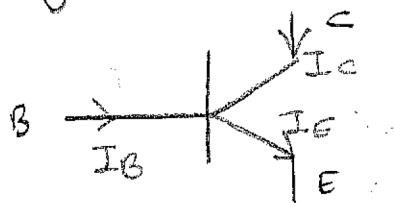
$$P_{AVG} = \frac{(3+1)mA \times (5V)}{2} = 10mW$$

## Bipolar Transistor Characteristics:

Transistor is an electronic device:



Symbol:



$I_B > 0 \rightarrow$  Transistor is ON.

$$I_E = I_B + I_C$$

But  $I_C = \beta \cdot I_B$ , where  $\beta = \text{gain}$  of the transistor,  
typically 100 or greater

$$\text{Therefore, } I_E = I_B + \beta I_B \approx \beta I_B$$

$$I_E \approx I_C$$

when  $I_B = 0, I_C = 0$  means that transistor is OFF.

$$\frac{I_B > 0}{\longrightarrow \downarrow} \quad I_C = \beta I_B$$

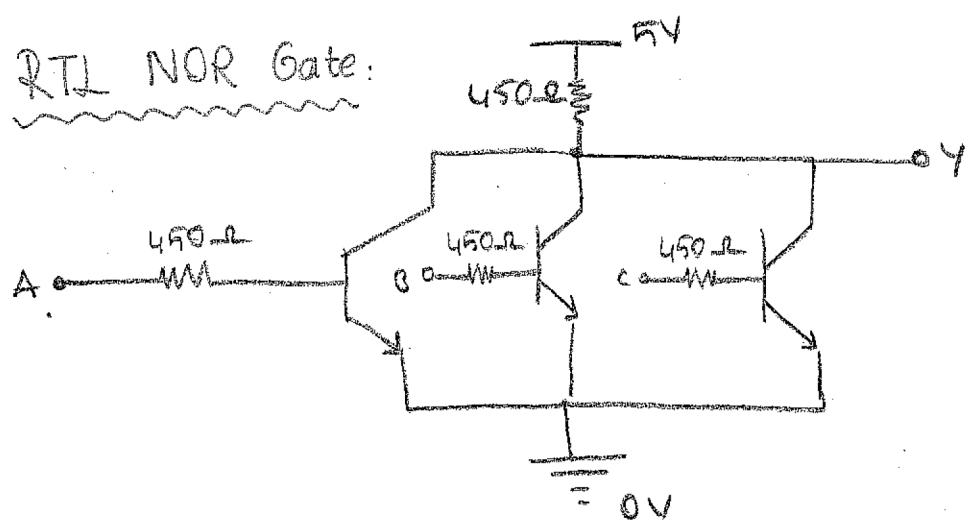
ON

$$\frac{I_B = 0}{\longrightarrow \uparrow} \quad I_C = 0$$

OFF

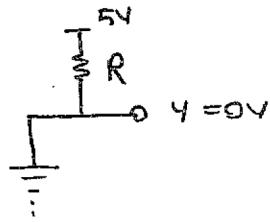
## RTL Circuits:

RTL NOR Gate:

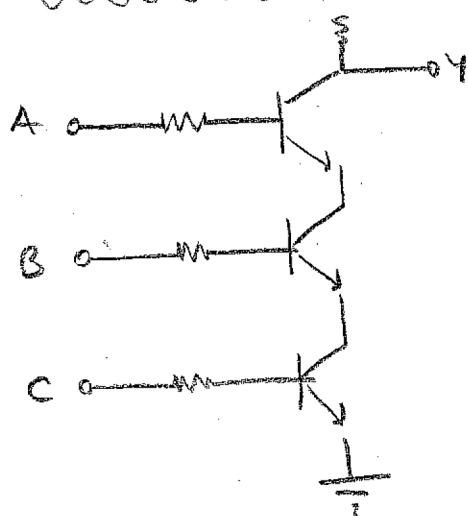


A	B	C	$(A+B+C)'$
0	0	0	1
0	0	1	0
0	1	0	0
1	0	0	0
1	1	1	0

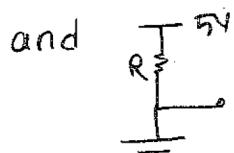
▼ When any of the inputs = 1  
Then;



RTL NAND Gate:



▼ When  $A=B=C=1$ .  
All trans. are ON.

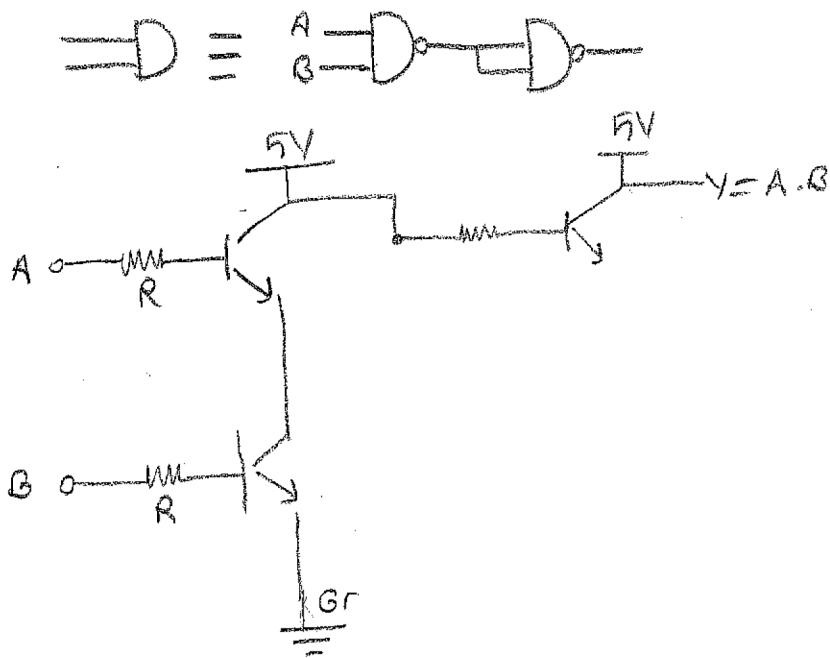


▼ If any input is "0",  $Y=1$   
say  $A=0$ ;  $Y=5V=1$

$$Y = 5V = 1$$

EX: Implement  $F = A \cdot B$  by using RTL logic.

The AND gate is;



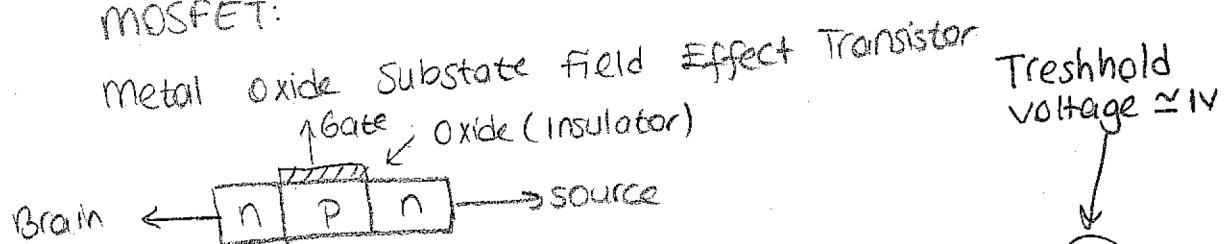
(RTL imp. of AND gate)

In computer architecture, CMOS logic is used, mostly becomes of low power consumption and fast switching.

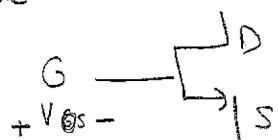
CMOS Logic:

Complementary MOSFET Transistor Logic

MOSFET:



The Symbols:

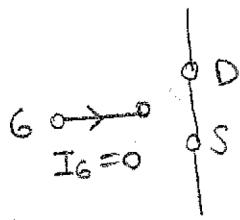


$V_{DS} < V_+$   
Trans is OFF!

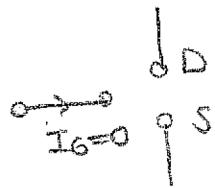
$V_{DS} > V_+$   
Trans is ON!

Threshold voltage  $\approx 1V$

Transistor is ON:



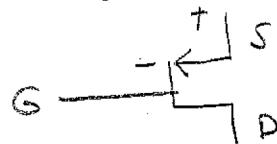
Transistor is OFF:



There is also; PMOS;



The symbol is;

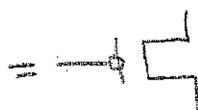


$$V_{DS} > V_+$$

Trans is ON!

$$V_{DS} < V_+$$

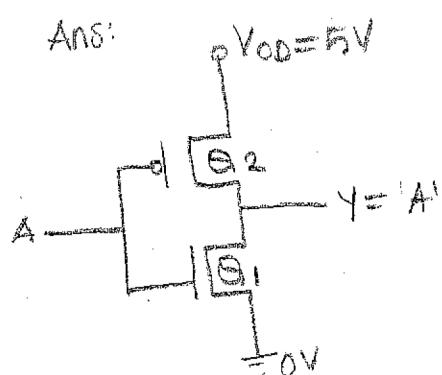
Trans is OFF!



$$\boxed{\text{CMOS} = \text{NMOS} + \text{PMOS}}$$

Ex: Implement an inverter using CMOS logic

Ans:



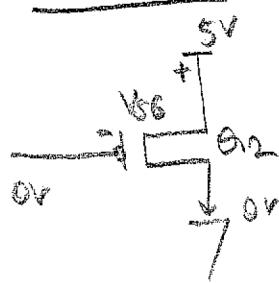
when  $A=0=0V$



$$V_{DS} = V_D - V_S = 0 - 0 = 0V$$

$0V < V_+ = 2V$ , Then  $\theta_1$  is OFF.

when  $A=0$



$$V_{SD} = V_S - V_D$$

$$= 5 - 0 = 5V > 2V \Rightarrow \theta_2 \text{ is ON}$$

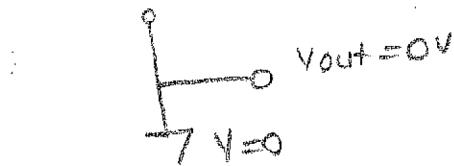
so when  $A=0$

$$V_{out} = 5V \approx 1^*$$

when  $A=1$ ,  $\Theta_1$  is ON,  $\Theta_2$  is OFF.

and

$$\overline{V_{DD}} = 5V$$



Thus;

A	Y
0	1
1	0

EX: Build an  $F = A \oplus B$  by using a cmos logic.  
(Assume complemented inputs are available)

Ans:

$$F = A \oplus B = \underbrace{AB'}_{\text{serial}} + \underbrace{A'B}_{\text{parallel}}$$

